



501.39932X00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: J. NOGUCHI, et al.
Application No.: 09/825,946
Filed: April 5, 2001
For: SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE AND
FABRICATION METHOD FOR SEMICONDUCTOR
INTEGRATED CIRCUIT DEVICE
Art Group: 2811
Examiner: H. Vu

RECEIVED
AUG 26 2002
TECHNOLOGY CENTER 2800
#8/a
9/4/02
jun

AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

August 22, 2002

Sir:

In response to the Office Action of May 22, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel Claims 36 and 39 - 41

Please amend Claim 20 as follows:

20. (Amended) A method of fabricating a semiconductor integrated circuit device comprising:

- ai
- (a) providing a semiconductor substrate having a first main surface,
 - (b) forming a first insulating film over said first main surface of said

semiconductor substrate,